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Uzodinma Okoroanyanwu, a research associate professor in the department of polymer science and engineering of University of Massachusetts at Amherst, conducts research aimed at developing materials and devices used in electrochemical energy storage; chemical sensing; printed, flexible, flexible/hybrid and wearable electronics; and electromagnetic interference shielding. He is an SPIE Fellow and an associate editor of the *Journal of Micro/Nanopatterning, Materials, and Metrology*. He is also the founder of Enx Labs, a company that translates his research results into devices and instruments that help to improve the human condition and sustain the environment. He worked previously at Advanced Micro Devices, where he spent 12 years conducting research on advanced lithography and organic polymer memories, and at GLOBALFOUNDRIES, where he spent 4 years conducting research on advanced lithography. He is the author of several books, including *Chemistry and Lithography*, *2nd edition, Vol. 1*: *The Chemical History of Lithography* (SPIE Press, 2020); *Molecular Theory of Lithography* (SPIE Press, 2015); and *Chemistry and Lithography* (SPIE Press & John Wiley & Sons, 2010). A holder of 37 U.S patents, he was educated at The University of Texas at Austin, where he earned the following degrees: Ph.D. physical chemistry (1997), M.S. chemical engineering (1995), M.A. physical chemistry (1994), B.S. chemistry and chemical engineering (1991).